

FORM PTO-1449 (SUBSTITUTE) U.S. DEPARTMENT OF COMMERCE PATENT AND TRADEMARK OFFICE				Attorney Docket No.: Applic. No. MUH-12041 09/997,983			
INFORMATION DISCLOSURE STATEMENT BY APPLICANT (37 CFR 1.98(b))				Applicant <div style="text-align: center;">Heinz Hönigschmid</div>			
Filing Date November 29, 2001				Group Art Unit <div style="text-align: center;">2818 2185</div>			

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U.S. PATENT DOCUMENTS							
EXAMINER INITIALS		PATENT NO.	DATE	PATENTEE	CLASS	SUB CLASS	FILING DATE
TP	A	5,940,319	08/17/99	Durlam et al.			
TP	B	6,097,625	08/01/00	Scheuerlein			
	C						
	D						
	E						
	F						
	G						
	H						
	I						

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FOREIGN PATENT DOCUMENT							
		DOCUMENT NO.	DATE	COUNTRY	CLASS	SUB CLASS	TRANSL. YES NO
	J						
	K						
	L						
	M						
	N						

OTHER DOCUMENTS (Including Author, Title, Date, Pertinent Pages, etc.)		
TP	O	M. Durlam et al.: "Nonvolatile RAM based on Magnetic Tunnel Junction Elements", 2000 IEEE International Solid-State Circuits Conference, Digest of Technical Papers, pp. 130-131.
TP	P	S. Tehrani et al.: "Recent Developments in Magnetic Tunnel Junction MRAM", IEEE Transactions on Magnetics, Vol. 36, No. 5, September 2000, pp. 2752-2757.
EXAMINER		DATE CONSIDERED
Trong Phan		9/28/03

EXAMINER: Initial if citation considered, whether or not citation is in conformance with MPEP 609; Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.